



HFZT

BC556 / BC557 / BC558

TO-92 Plastic-Encapsulate Transistors

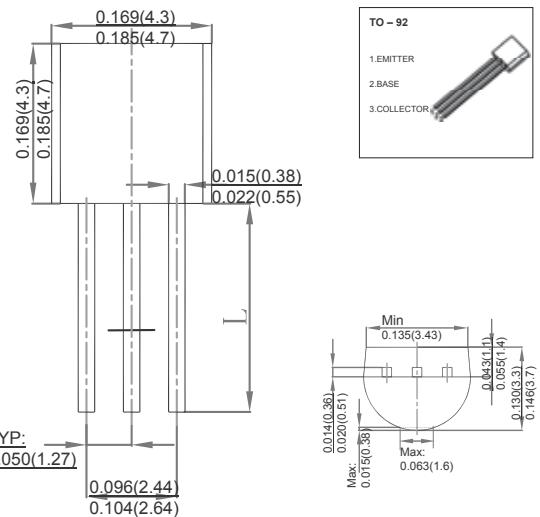
FEATURES

- High Voltage
- Complement to BC546, BC547, BC548
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter		Value	Unit		
V_{CBO}	Collector-Base Voltage	BC556	-80		V	
		BC557	-50			
		BC558	-30			
V_{CEO}	Collector-Emitter Voltage	BC556	-65		V	
		BC557	-45			
		BC558	-30			
V_{EBO}	Emitter-Base Voltage		-5	V		
I_c	Collector Current-Continuous		-0.1	A		
P_c	Collector Power Dissipation		625	mW		
R_{JJA}	Thermal Resistance from Junction to Ambient		200	°C/W		
T_j	Junction Temperature		150	°C		
T_{stg}	Storage Temperature		-55~+150	°C		

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-80			V
			-50			
			-30			
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2\text{mA}, I_B = 0$	-65			V
			-45			
			-30			
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -70\text{V}, I_E = 0$			-0.1	μA
					-0.1	μA
					-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -60\text{V}, I_B = 0$	-65			V
			-45			
			-30			
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	120		800	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$			-0.3	V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$			-0.65	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$			-0.8	V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	-0.55		-0.7	V
		$V_{CE} = -5\text{V}, I_C = -10\text{mA}$			-0.82	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			6	pF
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$		150		MHz
				150		MHz
				150		MHz

CLASSIFICATION of h_{FE}

RANK	A	B	C
RANGE	120-220	180-460	420-800